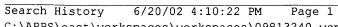
L Number		Search Text	DB	Time stamp
1	13	czochralski and (noble or inert or argon)	USPAT;	2002/06/20 13:51
		near4 mbar	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	i
2	2	("6291874").PN.	USPĀT;	2002/06/20 14:11
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
3	2	("6299892").PN.	USPAT;	2002/06/20 15:37
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
4	3	(zone-drawing or zone adj drawing) near12	USPAT;	2002/06/20 16:07
		czochralski	US-PGPUB;	1
			EPO; JPO;	
			DERWENT;	•
			IBM TDB	
5	6	(("6291874") or ("4330361")).PN.	USPAT;	2002/06/20 16:07
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	1154	((257/620) or (438/906) or (437/83) or	USPAT;	2002/06/20 11:43
	==	(437/84) or (117/19) or (117/84)).CCLS.	US-PGPUB;	
1		(33,731, 31 (22,727, 32 (21,733,7,3323)	EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	1	((("257/620") or ("438/906") or ("437/83")	USPAT;	2002/01/05 19:09
	-	or ("437/84") or ("117/19") or	US-PGPUB;	2002/01/03 13.03
		("117/84")).CCLS.) and (hydrogen with	EPO; JPO;	
		dop\$3 with silicon with wafer) same	DERWENT;	
		concentration	IBM TDB	
_	90		USPAT;	2002/01/05 19:10
	50	or ("437/84") or ("117/19") or	US-PGPUB;	2002/01/03 13.10
		("117/84")).CCLS.) and czochralski	EPO; JPO;	
		(117/04 //:colb.) and czochialski	DERWENT;	
			IBM TDB	
_	18	((("257/620") or ("438/906") or ("437/83")	USPAT;	2002/01/05 19:11
	10	or ("437/84") or ("117/19") or	US-PGPUB;	, 2002/01/05 19.11
		("117/84")).CCLS.) and heat adj shield	EPO; JPO;	!
		(117/64)).ccms.) and heat adj shield	DERWENT;	
			IBM TDB	
1_	27	///#257/620#\ or /#/20/006#\ or /#/27/02#\	_	2002/01/05 10:11
_	37	((("257/620") or ("438/906") or ("437/83")	USPAT;	2002/01/05 19:11
		or ("437/84") or ("117/19") or ("117/84")).CCLS.) and nitrogen with dop\$3	US-PGPUB; EPO; JPO;	
		(11//04 //.cobs./ and nitrogen with dop\$3		
			DERWENT;	
	4.2	((/#257/620#) on /#420/006#) on /#427/02#\	IBM_TDB	2002/01/05 19:12
_	43		USPAT;	2002/01/05 19:12
		or ("437/84") or ("117/19") or	US-PGPUB;	
		("117/84")).CCLS.) and (argon with	EPO; JPO;	
		hydrogen)	DERWENT;	
	221	/// / / / / / / / / / / / / / / / / / /	IBM_TDB	0000/01/05 10 10
-	201	((("257/620") or ("438/906") or ("437/83")	USPAT;	2002/01/05 19:12
i II		or ("437/84") or ("117/19") or	US-PGPUB;	
The state of the s		("117/84")).CCLS.) and oxidation	EPO; JPO;	
			DERWENT;	
			IBM_TDB	1 2002 (01 (05 10 14
<u> </u>	1	single adj silicon adj crystal.ti,ab. and	USPAT;	2002/01/05 19:14
1)	czochralski.ti,ab. and nitrogen.ti,ab.	US-PGPUB;	
	V		EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	54		USPAT;	2002/01/05 19:14
		czochralski.ti,ab. and nitrogen.ti,ab.	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	



				10000 100 100 100
-	805	(117/13).CCLS.	USPAT; US-PGPUB;	2002/01/05 19:17
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
_	0	(("117/13").CCLS.) and heat adj	USPĀT;	2002/01/05 19:17
		sjield.ti,ab. and czochralski	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
	_	(("117/13").CCLS.) and heat adj	IBM_TDB USPAT;	1 2002/01/05 19:17
_	5	shield.ti,ab. and czochralski	US-PGPUB;	2002/01/03 13:17
		Shield. Cl, ab. and Czochialski	EPO; JPO;	
i i			DERWENT;	
			IBM TDB	
_	43	trench adj mosfet.ti.	USPAT;	2002/01/05 20:15
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
	_		IBM_TDB	0000/01/05 00 15
-	9	(trench adj mosfet.ti.) and 257/\$6.ccls.	USPAT;	2002/01/05 20:15
			US-PGPUB; EPO; JPO;	
			DERWENT;	A.
			IBM TDB	
_	4	"6191009"	USPAT;	2002/01/29 12:24
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
	_	(1150400011)	IBM_TDB	0000/01/00 10:05
-	5	(("6191009") or ("6299982") or ("5942032")	USPAT	2002/01/29 12:25
1	_	or ("6224668") or ("6197109")).PN. (("6191009") or ("6299982") or ("5942032")	USPAT	2002/02/01 11:22
-	5	or ("6244668") or ("6197109")).PN.	OSFAI	2002/02/01 11.22
-	1	("6224668").PN.	USPAT	2002/02/01 11:29
1 _	4	("4210486").PN.	USPAT;	2002/06/11 16:22
		,	US-PGPUB;	
			EPO; JPO;	}
			DERWENT;	
1		l	IBM_TDB	0000 (06 (11 16 00
-	410		USPAT;	2002/06/11 16:23
		lcd).ti. and 257/\$6.ccls.	US-PGPUB; EPO; JPO;	
			DERWENT;	
l			IBM TDB	
1_	64	method.clm. and silicon.ti,ab. and	USPAT;	2002/06/19 17:56
	"	wafer.clm. and melt.clm. and (h or	US-PGPUB;	
1		hydrogen).clm. and (pressure near4 mbar)	EPO; JPO;	
1		(nitrogen near4 (doping or dopant or doped	DERWENT;	
		or dope)) and czochralski.ti,ab,clm.	IBM_TDB	2002/06/10 17 50
-	64	· ·	USPAT;	2002/06/19 17:59
		wafer.clm. and melt.clm. and hydrogen.clm.	US-PGPUB; EPO; JPO;	
		and (pressure near4 mbar) (nitrogen near4 (doping or dopant or doped or dope)) and	DERWENT;	
		czochralski.ti,ab,clm.	IBM TDB	1 1 1
1 -	1	method.clm. and silicon.ti,ab. and	USPAT;	2002/06/19 18:01
	1	wafer.clm. and melt.clm. and hydrogen.clm.	US-PGPUB;	
1		and (pressure near4 mbar) and (nitrogen	EPO; JPO;	
		near4 (doping or dopant or doped or dope))	DERWENT;	
		and czochralski.ti,ab,clm.	IBM_TDB	
1 -	1		USPAT;	2002/06/19 18:02
		wafer.clm. and melt.clm. and (h or	US-PGPUB;	
		hydrogen).clm. and (pressure near4 mbar)	EPO; JPO;	
		and (nitrogen near4 (doping or dopant or	DERWENT;	
	1	doped or dope)) and czochralski.ti,ab,clm. method.clm. and silicon.ti,ab. and	IBM_TDB USPAT;	2002/06/19 18:03
1-	1	wafer.clm. and (h or hydrogen).clm. and	US-PGPUB;	2002,00,13 10.03
		(pressure near4 mbar) and (nitrogen near4	EPO; JPO;	
		(doping or dopant or doped or dope)) and	DERWENT;	
		czochralski.ti,ab,clm.	IBM TDB	

-	1	method.clm. and silicon.ti,ab. and (h or hydrogen).clm. and (pressure near4 mbar)	USPAT; US-PGPUB;	2002/06/19 18:03
		and (nitrogen near4 (doping or dopant or doped or dope)) and czochralski.ti,ab,clm.	EPO; JPO; DERWENT; IBM TDB	
-	1	silicon.ti,ab. and (h or hydrogen).clm. and (pressure near4 mbar) and (nitrogen near4 (doping or dopant or doped or dope)) and czochralski.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/06/19 18:04
-	1	silicon and (h or hydrogen).clm. and (pressure near4 mbar) and (nitrogen near4 (doping or dopant or doped or dope)) and czochralski.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/06/19 18:05
-	1	silicon and (h or hydrogen) and (pressure near4 mbar) and (nitrogen near4 (doping or dopant or doped or dope)) and czochralski.ti,ab,clm.	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/06/19 18:06
-	1	silicon and (h or hydrogen) and (pressure near4 mbar) and (nitrogen near4 (doping or dopant or doped or dope)) and czochralski	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/06/19 18:06
-	1	silicon and (h or hydrogen) and (pressure near5 mbar) and (nitrogen near5 (doping or dopant or doped or dope)) and czochralski	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/06/19 18:07
-	22	silicon and (h or hydrogen) and pressure and (nitrogen near5 (doping or dopant or doped or dope)) and czochralski	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/06/19 19:20
-	5	czochralski and pressure near3 mbar and oxygen	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/06/19 19:21
_	23	czochralski.ti,ab. and pressure near3 argon	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/06/19 20:37
-	5	czochralski.ti,ab. and pressure near3 argon near3 mbar	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/06/19 20:37
-	0	czochralski.ti,ab. and pressure near3 argon near3 mbar near3 hydrogen	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/06/19 20:38
-	3	czochralski.ti,ab. and pressure near3 mbar near3 hydrogen	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/06/19 20:38
_	3	czochralski.ti,ab. and pressure near3 mbar near3 hydrogen and silicon.ti,ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/06/19 20:39
-	3	czochralski.ti,ab. and pressure near3 mbar near3 argon and silicon.ti,ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/06/19 20:39